

# RT3NGGM

Composite Transistor With Resistor  
For Switching Application  
Silicon Epitaxial Type

## DESCRIPTION

RT3NGGM is composite transistor built with two RT1N432 chips in SC-88 package.

## FEATURE

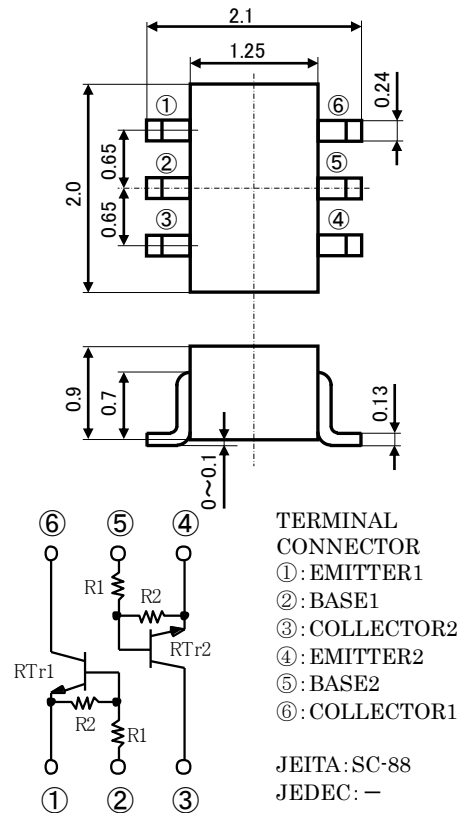
- Silicon epitaxial type
- Each transistor elements are independent.
- Mini package for easy mounting

## APPLICATION

- Inverted circuit, Switching circuit,
- Interface circuit, Driver circuit

## OUTLINE DRAWING

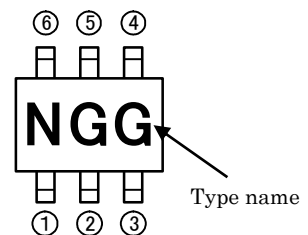
Unit:mm



## MAXIMUM RATING(T<sub>a</sub>=25°C)(R<sub>Tr1</sub>, R<sub>Tr2</sub> COMMON)

SYMBOL	PARAMETER	RATING	UNIT
V <sub>CB0</sub>	Collector to Base voltage	50	V
V <sub>EBO</sub>	Emitter to Base voltage	7	V
V <sub>CEO</sub>	Collector to Emitter voltage	50	V
V <sub>IN</sub>	Input voltage	20	V
I <sub>C</sub>	Collector current	100	mA
I <sub>CM</sub>	Peak Collector current	200	mA
P <sub>T</sub>	Total dissipation	200	mW
T <sub>j</sub>	Junction temperature	+150	°C
T <sub>stg</sub>	Storage temperature	-55~+150	°C

## MARKING



## ELECTRICAL CHARACTERISTICS(T<sub>a</sub>=25°C)(R<sub>Tr1</sub>, R<sub>Tr2</sub> COMMON)

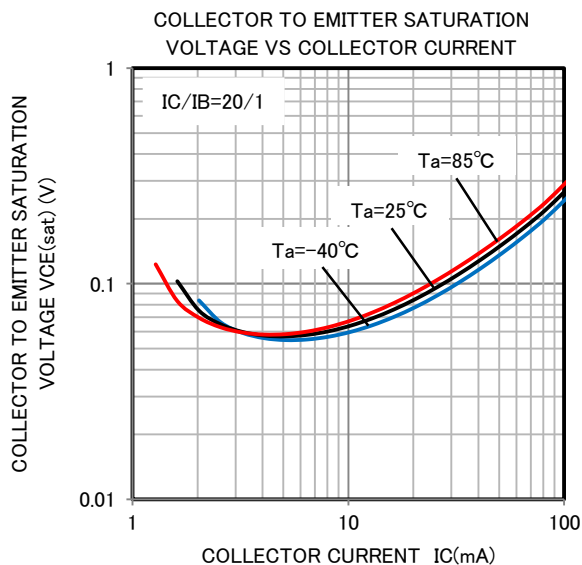
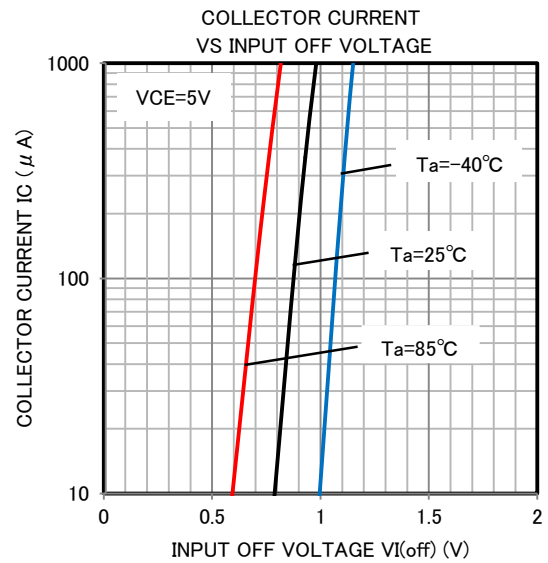
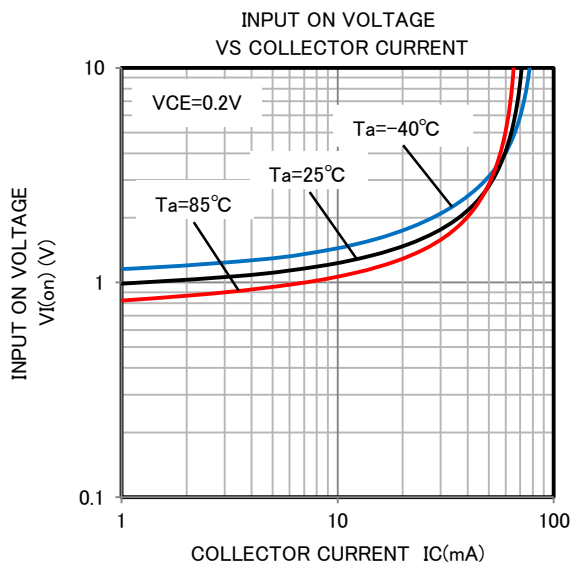
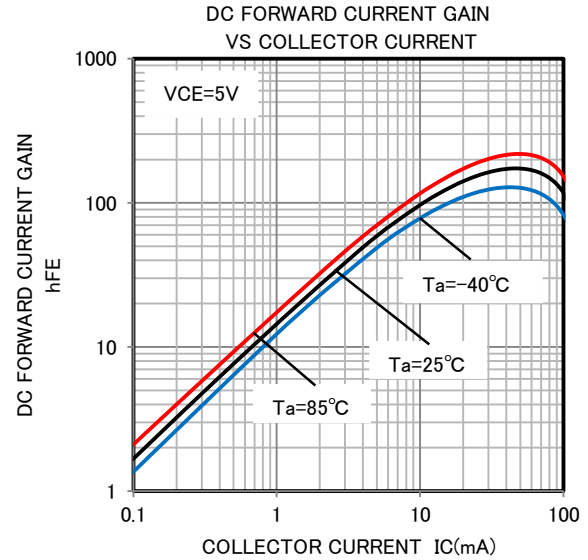
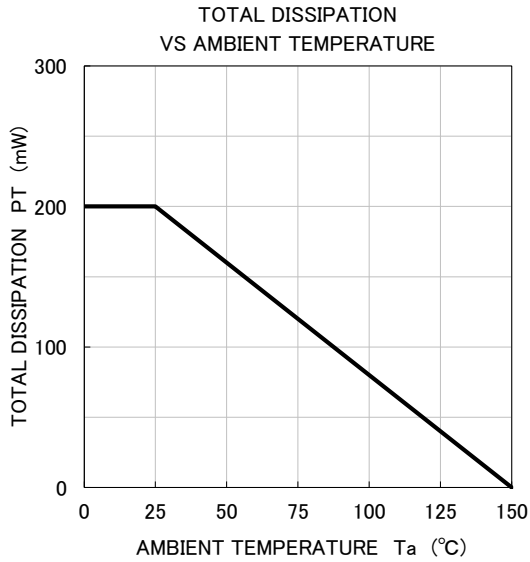
SYMBOL	PARAMETER	TEST CONDITIONS	LIMITS			UNIT
			MIN	TYP	MAX	
V <sub>(BR)CEO</sub>	Collector to Emitter breakdown voltage	I <sub>C</sub> =100μA, R <sub>BE</sub> =∞	50	-	-	V
I <sub>CB0</sub>	Collector cut off current	V <sub>CB</sub> =50V, I <sub>E</sub> =0	-	-	0.1	μA
I <sub>EBO</sub>	Emitter cut off current	V <sub>EB</sub> =5V, I <sub>C</sub> =0	255	340	493	μA
h <sub>FE</sub>	DC forward current gain	V <sub>CE</sub> =5V, I <sub>C</sub> =10mA	30	-	-	-
V <sub>CE(sat)</sub>	Collector to Emitter saturation voltage	I <sub>C</sub> =10mA, I <sub>B</sub> =0.5mA	-	0.1	0.3	V
V <sub>I(ON)</sub>	Input on voltage	V <sub>CE</sub> =0.2V, I <sub>C</sub> =5mA	-	1.0	1.8	V
V <sub>I(OFF)</sub>	Input off voltage	V <sub>CE</sub> =5V, I <sub>C</sub> =100μA	0.5	0.8	-	V
R <sub>1</sub>	Input resistor	-	3.3	4.7	6.1	kΩ
R <sub>2</sub> /R <sub>1</sub>	Resistor ratio	-	1.7	2.1	2.6	-
f <sub>T</sub>	Gain band width product	V <sub>CE</sub> =6V, I <sub>E</sub> =10mA	-	200	-	MHz

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## TYPICAL CHARACTERISTICS

(RT<sub>1</sub>, RT<sub>2</sub> COMMON)



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